



## Description

The STD6NF10 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

$V_{DS} = 100V, I_D = 10A$

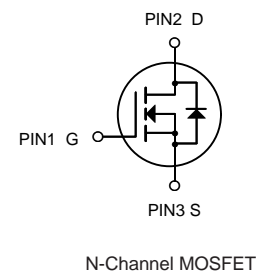
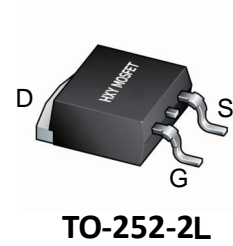
$R_{DS(ON)} < 160m\Omega @ V_{GS}=10V$

$R_{DS(ON)} < 170m\Omega @ V_{GS}=4.5V$

High density cell design for ultra low  $R_{dson}$

Fully characterized avalanche voltage and current

Excellent package for good heat dissipation



## Application

Power switching application

Hard switched and high frequency circuits

Uninterruptible power supply

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
STD6NF10	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	10	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	40	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.75	$^\circ C/W$



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0		2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	140	160	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	160	170	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	-	5	-	S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C <sub>oss</sub>		-	25	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	20	-	PF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, R <sub>L</sub> =19Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	20	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	20.6		nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.3	-	nC
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	7	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



### Typical Electrical and Thermal Characteristics (Curves)

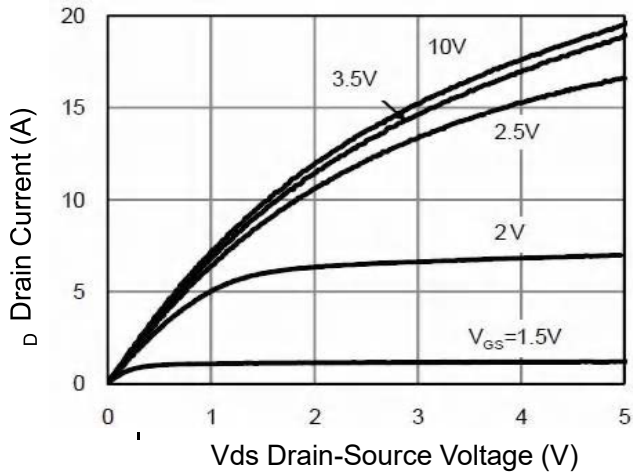


Figure 1 Output Characteristics

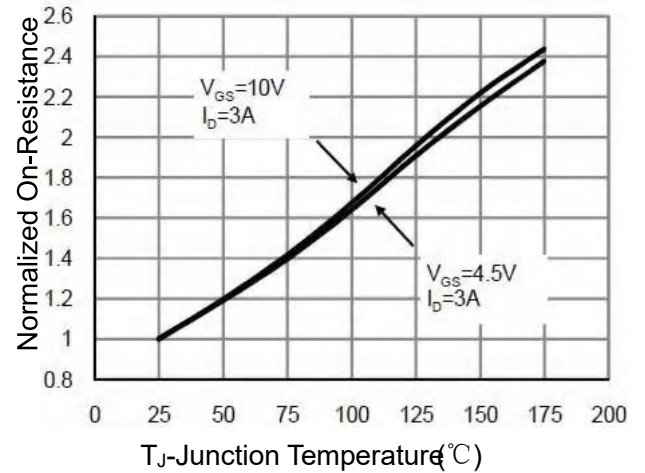


Figure 4 Rdson-Junction Temperature

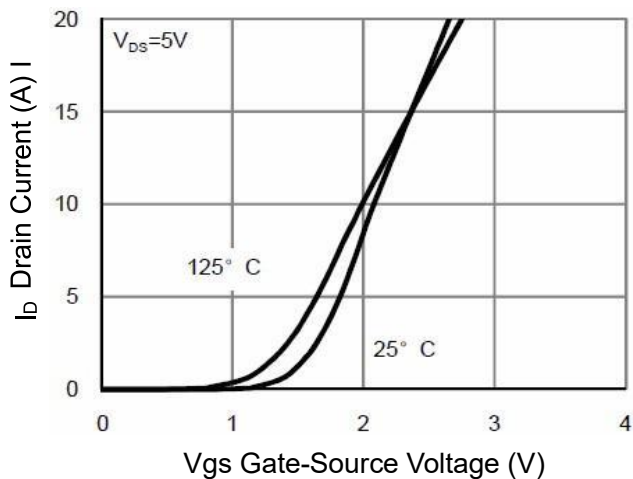


Figure 2 Transfer Characteristics

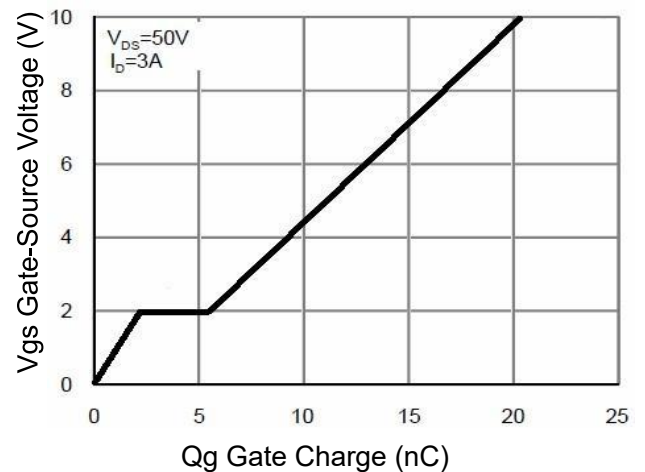


Figure 5 Gate Charge

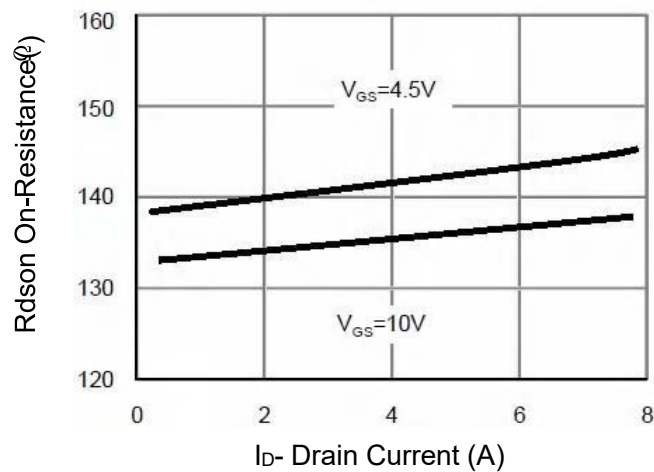


Figure 3 Rdson-Drain Current

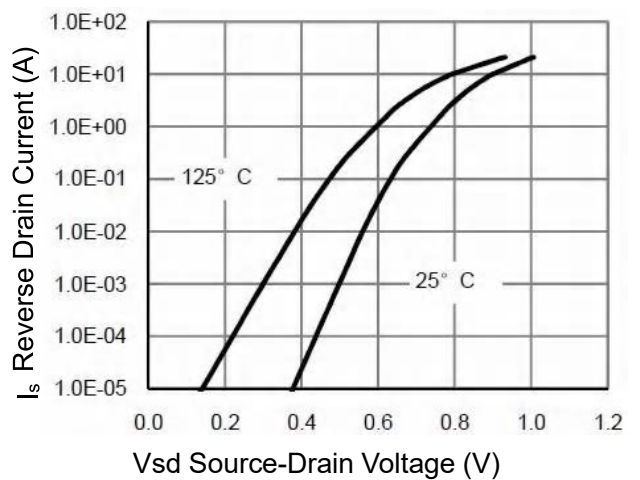


Figure 6 Source- Drain Diode Forward

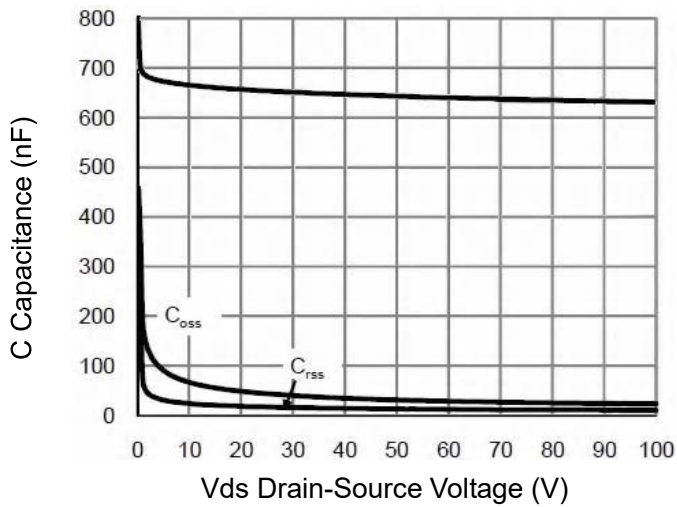


Figure 7 Capacitance vs Vds

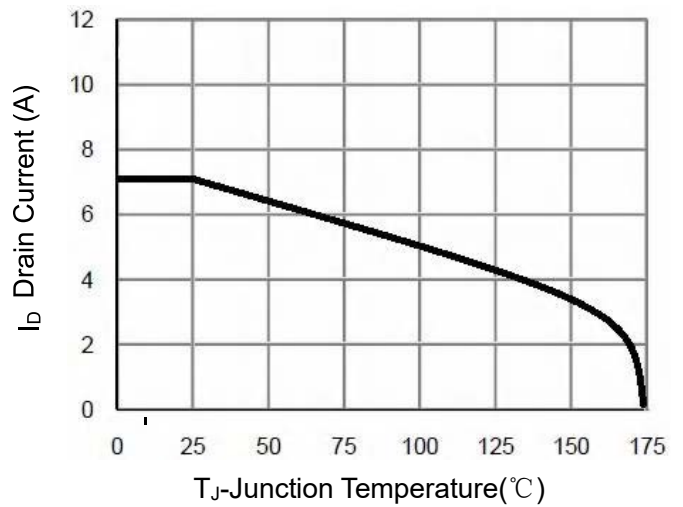


Figure 9  $BV_{DSS}$  vs Junction Temperature

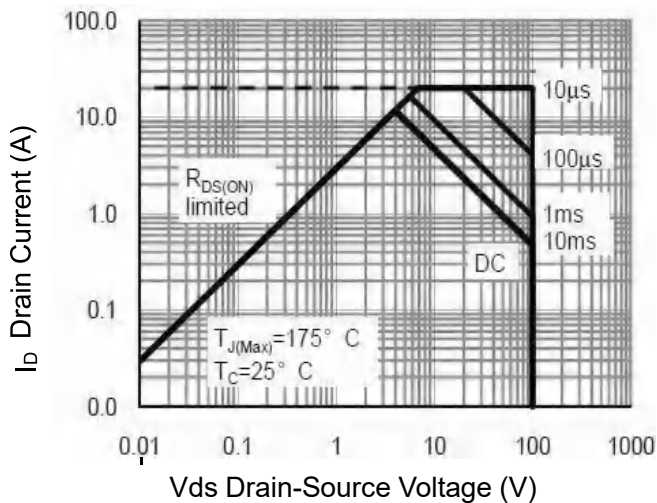


Figure 8 Safe Operation Area

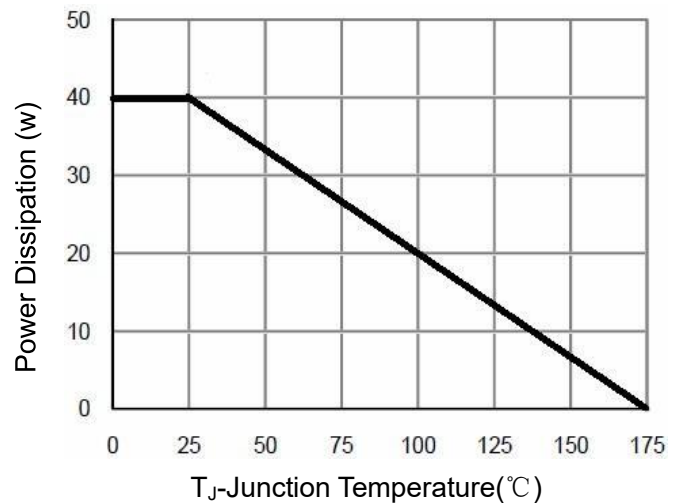


Figure 10 Power De-rating

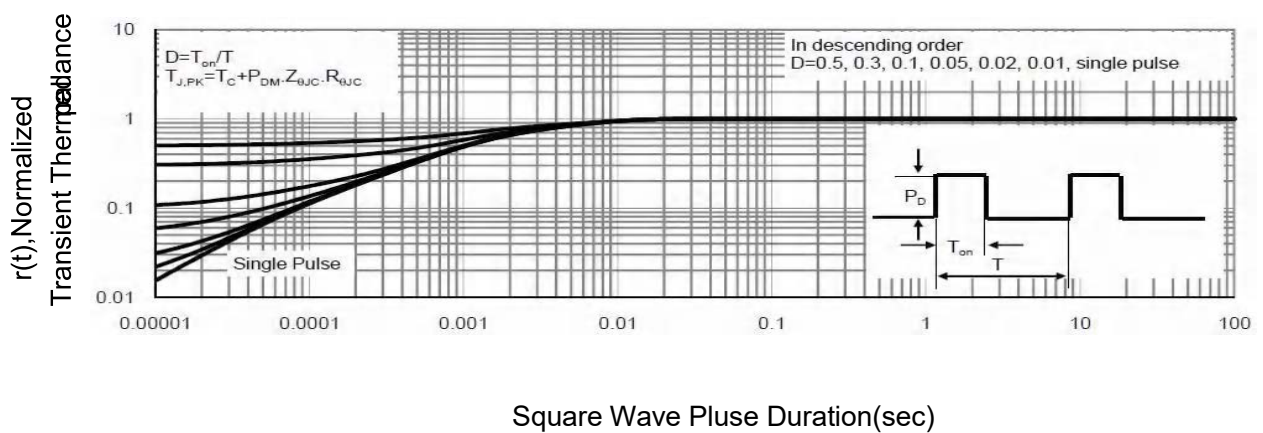


Figure 11 Normalized Maximum Transient Thermal Impedance





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